N-Channel 60-V (D-S) MOSFET

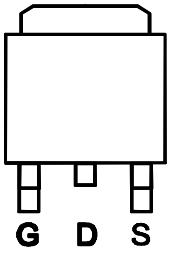
General Description

The B6010D is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching and low in-line power loss are needed in a very small outline surface mount package.

Features

- **$R_{DS(ON)}$=90mΩ@V_{GS}=10V**
- **$R_{DS(ON)}$=120mΩ@V_{GS}=4.5V**
- **Super High Density Cell Design for Extremely Low $R_{DS(ON)}$**
- **Exceptional On-Resistance and Maximum DC Current**
- **SOP-8 Package**

Pin Configuration



Applications

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC

Absolute Maximum Ratings (TA=25℃ Unless Otherwise Noted):

Parameter		Symbol	N-Channel	Unit
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(tJ=150℃)	TA=25℃	I_D	12	A
	TA=70℃		9	
Pulsed Drain Current		I_{DM}	30	A
Continuous Source Current (Diode Conduction)		I_S	1.7	A
Maximum Power Dissipation	TA=25℃	P_D	2.0	W
	TA=70℃		1.44	
Operating Junction Temperature		T_J	-55 to 150	℃
Thermal Resistance-Junction to Case		RθJC	48	℃/W